

CLAIM AMENDMENTS

1.-35. (Cancelled)

36. (Original) A semiconductor structure comprising:

a substrate containing a germanium region;

a metal contact; and

a germanide layer located between the germanium region and the metal contact.

37. (Original) The semiconductor structure of claim 36, wherein the germanide layer contacts the metal contact and the germanium region.

38. (Original) The semiconductor structure of claim 36, wherein the germanide layer comprises a nickel germanide layer.

39. (Original) The semiconductor structure of claim 36, wherein the germanide layer comprises a silicon germanide layer.

40. (Original) The semiconductor structure of claim 36, wherein the metal contact is associated with one of a source and a drain of a transistor.

41. (New) An apparatus comprising:

a transistor drain region;

a transistor source region;

a first metal contact;

a second metal contact;

a first germanide layer located between a germanium region of a semiconductor structure and the first metal contact; and

a second germanide layer located between the germanium region and the second metal contact.

42. (New) The apparatus of claim 41, wherein the germanide layer contacts the metal contact and the germanium region.

43. (New) The apparatus of claim 41, wherein the germanide layer comprises a nickel germanide layer.

44. (New) The apparatus of claim 41, wherein the germanide layer comprises a silicon germanide layer.

45. (New) The apparatus of claim 41, further comprising:
a silicide region; and
a transistor gate region in contact with the silicide region.

46. (New) The apparatus of claim 45, wherein the silicide region comprises a nickel silicide region.